

Title (en)
CAPACITOR ELECTRODE STRUCTURE

Title (de)
KONDENSATORELEKTRODENANORDNUNG

Title (fr)
STRUCTURE ELECTRODE DE CONDENSATEUR

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Application
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Abstract (en)
[origin: WO0039842A1] The invention relates to a microelectronic structure. In said structure, an oxygen-containing iridium layer (25) is embedded between a silicon-containing layer (8, 20) and an oxygen barrier layer (30). Said iridium layer is especially produced by a sputter process in an oxygen atmosphere with a low oxygen content. The oxygen-containing iridium layer (25) is stable at temperatures up to 800 DEG C and withstands the formation of iridium silicide upon contact with the silicon-containing layer (20). Such microelectronic structures are preferably used in semiconductor memories.

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IPC 8 full level
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